# **MMDT4126**



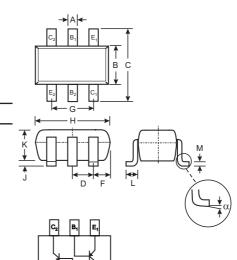
## **DUAL PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR**

### **Features**

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMDT4124)
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 3)

### **Mechanical Data**

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking (See Page 2): K2B
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)



SOT-363									
Dim	Min	Max							
Α	0.10	0.30							
В	1.15	1.35							
С	2.00	2.20							
D	0.65 N	Nominal							
F	0.30	0.40							
Н	1.80	2.20							
J	_	0.10							
K	0.90	1.00							
L	0.25	0.40							
M	0.10	0.25							
α	0°	8°							
All Dimensions in mm									

#### Maximum Ratings @ $T_A = 25$ °C unless otherwise specified

Characteristic	Symbol	MMDT4126	Unit	
Collector-Base Voltage	V <sub>CBO</sub>	-25	V	
Collector-Emitter Voltage	V <sub>CEO</sub>	-25	V	
Emitter-Base Voltage	V <sub>EBO</sub>	-4.0	V	
Collector Current - Continuous (Note 1)	I <sub>C</sub>	-200	mA	
Power Dissipation (Note 1, 2)	Pd	200	mW	
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	625	K/W	
Operating and Storage and Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C	

1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

- 2. Maximum combined dissipation.
- 3. No purposefully added lead.



### **Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol Min Max		Max	Unit	Test Condition					
OFF CHARACTERISTICS (Note 4)										
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-25	_	V	$I_C = -10\mu A, I_E = 0$					
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-25	_	V	I <sub>C</sub> = -1.0mA, I <sub>B</sub> = 0					
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-4.0	_	V	$I_E = -10\mu A, I_C = 0$					
Collector Cutoff Current	I <sub>CBO</sub>	_	-50	nA	V <sub>CB</sub> = -20V, I <sub>E</sub> = 0V					
Emitter Cutoff Current	I <sub>EBO</sub>	_	-50	nA	V <sub>EB</sub> = -3.0V, I <sub>C</sub> = 0V					
ON CHARACTERISTICS (Note 4)	-									
DC Current Gain	h <sub>FE</sub>	120 60	360 —	_	I <sub>C</sub> = -2.0mA, V <sub>CE</sub> = -1.0V I <sub>C</sub> = -50mA, V <sub>CE</sub> = -1.0V					
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	-0.40	V	I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA					
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	-0.95	V	I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA					
SMALL SIGNAL CHARACTERISTICS										
Output Capacitance	C <sub>obo</sub>	_	4.5	pF	$V_{CB} = -5.0V$ , $f = 1.0MHz$ , $I_E = 0$					
Input Capacitance	C <sub>ibo</sub>	_	10	pF	$V_{EB} = -0.5V$ , $f = 1.0MHz$ , $I_C = 0$					
Small Signal Current Gain	h <sub>fe</sub>	120	480	_	$V_{CE} = -1.0V, I_{C} = -2.0mA,$ f = 1.0kHz					
Current Gain-Bandwidth Product	f⊤	250	_	MHz	V <sub>CE</sub> = -20V, I <sub>C</sub> = -10mA, f = 100MHz					
Noise Figure	NF	_	4.0	dB	$V_{CE}$ = -5.0V, $I_{C}$ = -100 $\mu$ A, $R_{S}$ = 1.0k $\Omega$ , $f$ = 1.0kHz					

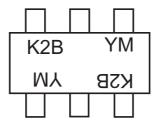
### Ordering Information (Note 5)

Device		Packaging	Shipping		
	MMDT4126-7-F	SOT-363	3000/Tape & Reel		

Notes: 4. Short duration test pulse used to minimize self-heating effect.

5. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**

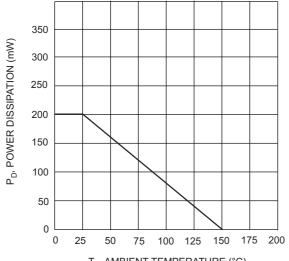


K2B = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

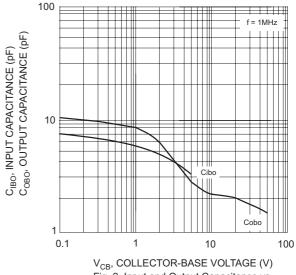
### Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	М	N	Р	R	S	Т	U	V	W
Month Jan Feb March Apr May Jun Jul Aug Sep Oct Nov Dec										Dec		
Month	oun	1 00	IVIGI OII	Abı	ividy	oun	oui	Aug	ОСР	001	1404	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

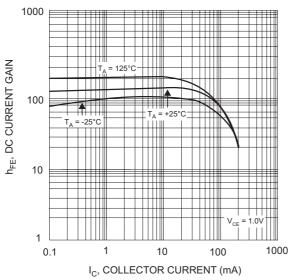




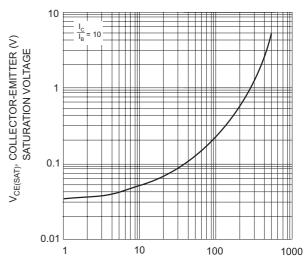
T<sub>A</sub>, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs Ambient Temperature



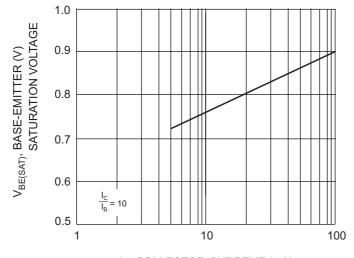
V<sub>CB</sub>, COLLECTOR-BASE VOLTAGE (V) Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 3, Typical DC Current Gain vs Collector Current



I<sub>C</sub>, COLLECTOR CURRENT (mA)
Fig. 4, Typical Collector-Emitter Saturation Voltage
vs. Collector Current



I<sub>C</sub>, COLLECTOR CURRENT (mA)
Fig. 5, Typical Base-Emitter
Saturation Voltage vs. Collector Current



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